

L Number	Hits	Search Text	DB	Time stamp
1	3643	(consum\$3 oxidizing oxidation oxidized oxidizable) with (spacer sidewall side adj wall) and (spacer sidewall side adj wall) with (masking masked mask)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/10 13:46
2	2747	(consum\$3 oxidizing oxidation oxidized oxidizable) with (spacer sidewall side adj wall) and (spacer sidewall side adj wall) with (masking masked mask) same (etch\$5)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/10 13:46
3	2188	(consum\$3 oxidizing oxidation oxidized oxidizable) with (spacer sidewall side adj wall) and (spacer sidewall side adj wall) with (masking masked mask) with (etch\$5)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/10 13:46
4	2059	(consum\$3 oxidizing oxidation oxidized oxidizable) with (spacer sidewall side adj wall) and (spacer sidewall side adj wall) with (masking masked mask) with (etch\$5) and (spacer sidewall side adj wall) with (silicon poly polysilicon si semiconductor)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/10 13:47
5	2060	(consum\$3 oxidizing oxidation oxidized oxidizable) with (spacer sidewall side adj wall) and (spacer sidewall side adj wall) with (masking masked mask) with (etch\$5) and (spacer sidewall side adj wall) with (silicon poly polysilicon si semiconductor oxidizable)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/10 13:47
6	659	(consum\$3 oxidizing oxidation oxidized oxidizable) with (spacer sidewall side adj wall) and (spacer sidewall side adj wall) with (masking masked mask) with (etch\$5) with (trench groove) and (spacer sidewall side adj wall) with (silicon poly polysilicon si semiconductor oxidizable)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/10 13:48
7	534	((consum\$3 oxidizing oxidation oxidized oxidizable) with (spacer sidewall side adj wall) and (spacer sidewall side adj wall) with (masking masked mask) with (etch\$5) with (trench groove) and (spacer sidewall side adj wall) with (silicon poly polysilicon si semiconductor oxidizable)) and (438/\$6 257/\$6)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/10 13:48
8	112	(consum\$3 oxidizing oxidation oxidized oxidizable) with (spacer sidewall side adj wall) and (spacer sidewall side adj wall) with (masking masked mask) with (etch\$5) with (second another) near4 (trench groove) and (spacer sidewall side adj wall) with (silicon poly polysilicon si semiconductor oxidizable)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/10 13:48
9	3376	(438/424,425,426,427,430,431,435,437).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/10 13:57
10	211	((consum\$3 oxidizing oxidation oxidized oxidizable) with (spacer sidewall side adj wall) and (spacer sidewall side adj wall) with (masking masked mask)) and ((438/424,425,426,427,430,431,435,437).CCLS.) not ((consum\$3 oxidizing oxidation oxidized oxidizable) with (spacer sidewall side adj wall) and (spacer sidewall side adj wall) with (masking masked mask) with (etch\$5) with (second another) near4 (trench groove) and (spacer sidewall side adj wall) with (silicon poly polysilicon si semiconductor oxidizable))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/10 13:58